

RoHS Compliant Product  
A suffix of "-C" specifies halogen & lead-free

**FEATURES**

- Two DTC114T chips in a package
- Transistor elements are independent, eliminating interference
- Mounting cost and area be cut in half

**MARKING**

**H4**

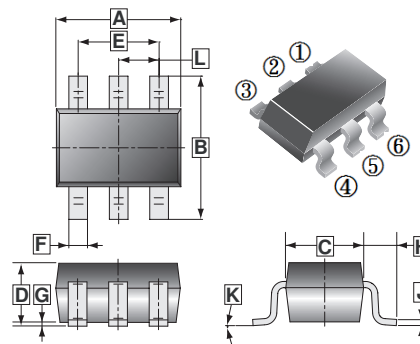
**PACKAGE INFORMATION**

Package	MPQ	Leader Size
SOT-363	3K	7 inch

**ORDER INFORMATION**

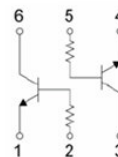
Part Number	Type
UMH4N	Lead (Pb)-free
UMH4N-C	Lead (Pb)-free and Halogen-free

**SOT-363**



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.80	2.20	G	0.100	REF.
B	1.80	2.45	H	0.525	REF.
C	1.15	1.35	J	0.08	0.25
D	0.80	1.10	K	8°	
E	1.10	1.50	L	0.650 TYP.	
F	0.10	0.35			

**EQUIVALENT CIRCUIT**



**ABSOLUTE MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	50	
Emitter-Base Voltage	$V_{EBO}$	5	
Collector Current	$I_C$	100	mA
Collector Dissipation	$P_C$	150	mW
Junction and Storage Temperature	$T_J, T_{STG}$	150, -55~150	$^{\circ}\text{C}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Collector-Base Breakdown Voltage	$V_{CBO}$	50	-	-	V	$I_C=50\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{CEO}$	50	-	-		$I_C=1\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{EBO}$	5	-	-		$I_E=50\mu\text{A}, I_C=0$
Collector Cut-Off Current	$I_{CBO}$	-	-	0.5	$\mu\text{A}$	$V_{CB}=50\text{V}, I_E=0$
Emitter Cut-Off Current	$I_{EBO}$	-	-	0.5	$\mu\text{A}$	$V_{EB}=4\text{V}, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.3	V	$I_C=10\text{mA}, I_B=1\text{mA}$
DC Current Gain	$h_{FE}$	100	300	600		$V_{CE}=5\text{V}, I_C=1\text{mA}$
Input Resistance	$R_1$	7	10	13	k $\Omega$	
Transition Frequency	$f_T$	-	250	-	MHz	$V_{CE}=10\text{V}, I_E=-5\text{mA}, f=100\text{MHz}$

**CHARACTERISTICS CURVE**

Static Characteristic

